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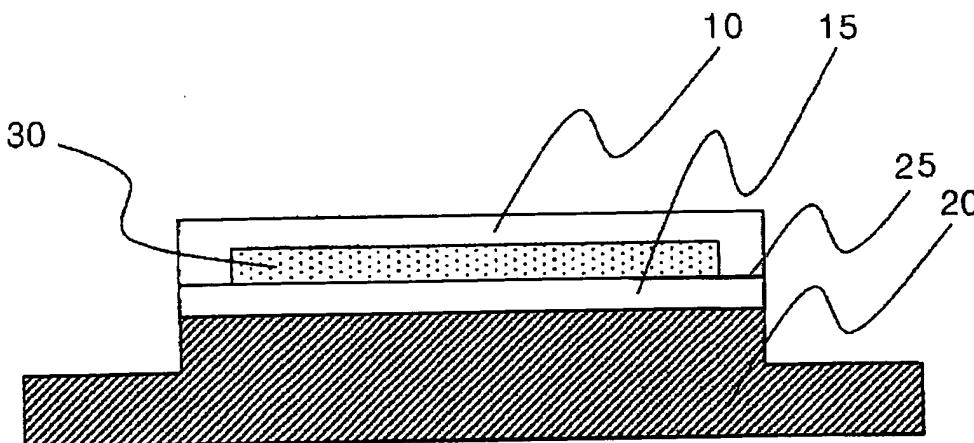
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(54) Title: ELECTRO-STATIC CHUCK WITH NON-SINTERED ALN AND A METHOD OF PREPARING THE SAME



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(57) Abstract: The present invention relates to an electro-static chuck with non-sintered AlN and a method of preparing the same. Especially, the present invention relates to the electro-static chuck with non-sintered AlN which having coated aluminum nitride (AlN) layer as a dielectric one on the purpose of chucking the wafers in the process of wafers and a method of preparing the same. The electro-static chuck of the present invention has excellent dielectric characteristics, bonding strength and thermal conductivity by forming an AlN layer as a dielectric one without sintering process or bonding process with binders.